

Supporting Information

Real-Time Tracking of Interfacial Charge Dynamics in a Metal–Dielectric Janus Nanocluster

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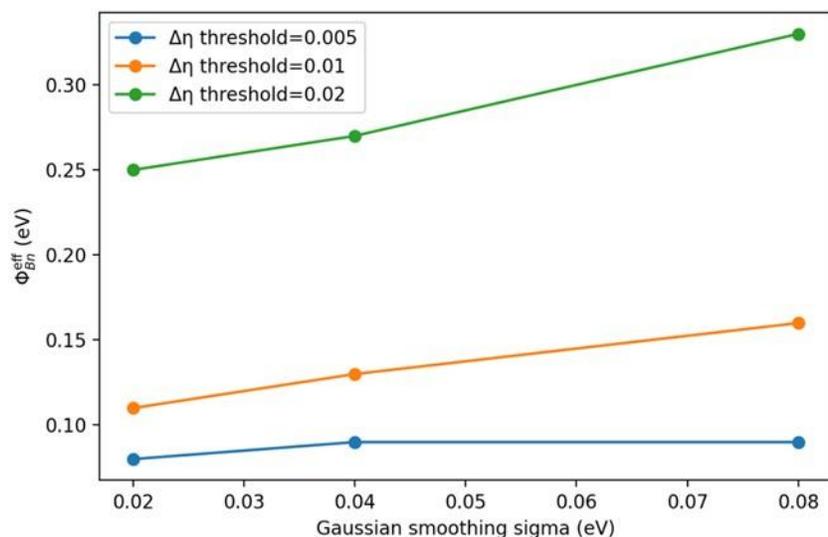


Figure S1. Dependence of the effective electron injection barrier, Φ_{Bn}^{eff} , on the excess injection threshold $\Delta\eta$ and Gaussian spectral broadening σ . The extracted barrier shows weak sensitivity to σ over the range 0.02 – 0.08eV.

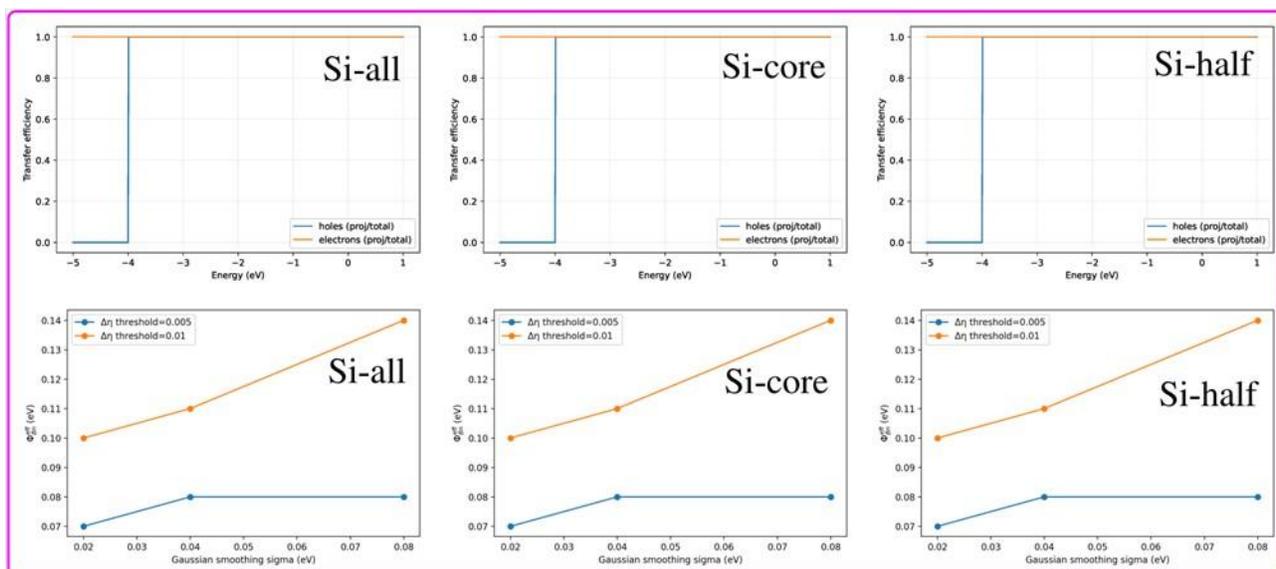


Figure S2. Transfer efficiency and effective injection barrier Φ_{Bn}^{eff} evaluated for different Si partitioning schemes (Si-all, Si-core, and Si-half), showing consistent near-Fermi injection behavior across partition choices.

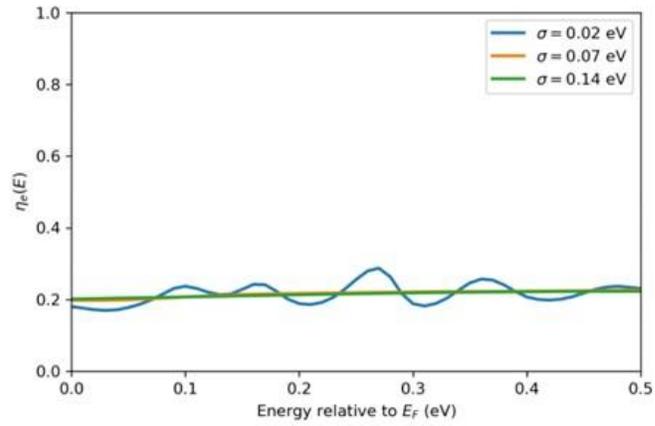


Figure S3. Si-resolved electron population $n_e(E)$ above E_F for different Gaussian broadenings ($\sigma = 0.02 - 0.14$ eV), showing robust near-Fermi injection.

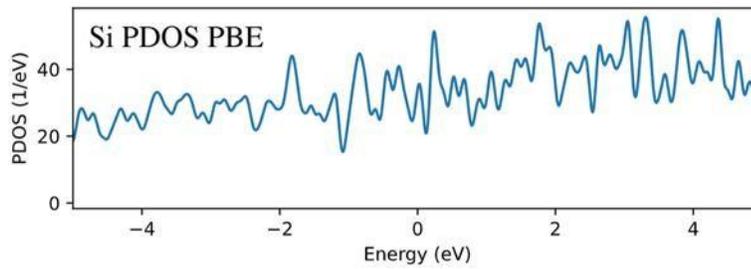


Figure S4. Si-projected density of states computed using the PBE functional.

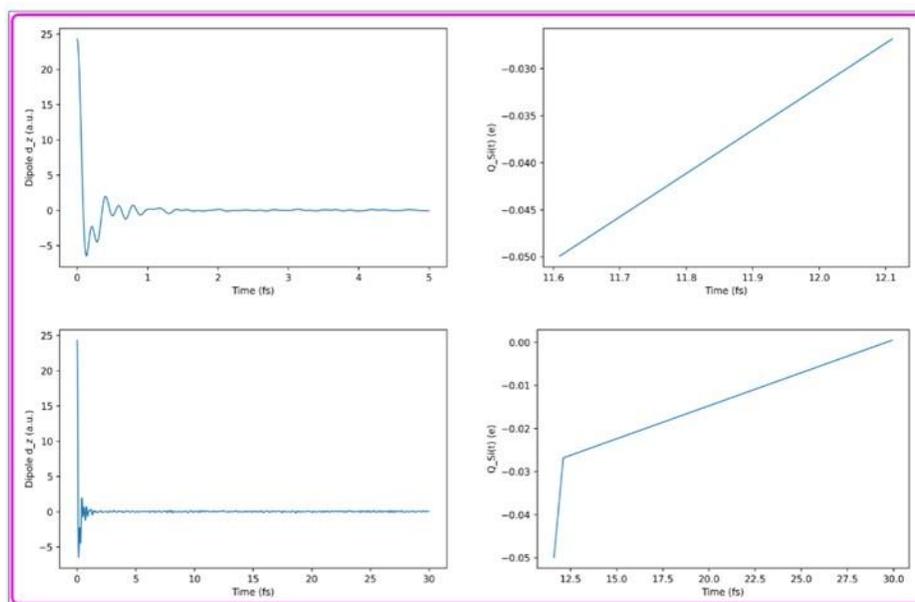


Figure S5. Time-resolved dipole moment and Si charge dynamics showing early-time coherent oscillations and subsequent electronic dephasing.

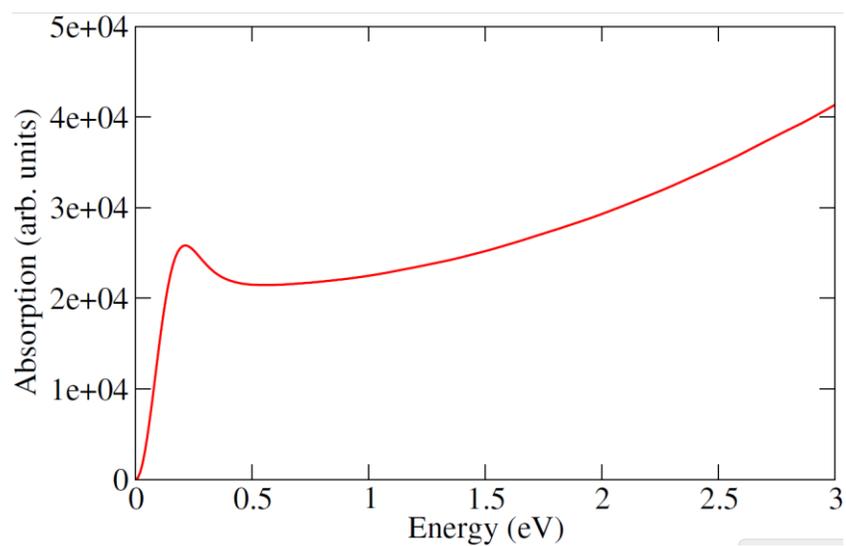


Figure S6. Absorption spectrum.

